

In 2D: Ferroelectric Switch of Electronic Topology, and the Flexo-Ferroelectricity of Actuator Motor

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The low dimensionality (of 1D nanowires [1] or 2D monolayers [2-4]) brings about two distinctly new features to ferroelectric: (I) its polarization \mathbf{P} can be along, longitudinal (\mathbf{P}_l) or perpendicular, transverse (\mathbf{P}_t) with respect to the material line or plane—a strong anisotropy due to low-D, absent for 3D crystals. (II) Compliance, to bend easily into “empty-dimension”, a new degree of freedom on display. We discuss examples, emerging from (I) and (II), where flipping intrinsic \mathbf{P} switches something else—the essence of multiferroics, where electrical and magnetic polarizations are coupled (also possible in low-D, e.g. in MXene [2]). We show how $\pm\mathbf{P}_t$ flip switches the topological state of 2DM [3] or, in very different manifestation, can alter the shape, performing as actuator [4].

We design and explore with DFT a hetero-bilayer of realistic 2D components of matching lattice symmetry, the β -phase antimonene β -Sb (known for its strong spin-orbit coupling) and ferroelectric In_2Se_3 . The $\pm\mathbf{P}$ of the In_2Se_3 induces distinctly different electronics in the bilayer: if \mathbf{P} points “inward”, the bilayer is a trivial insulator; when switched “outward”, its state is nontrivial topological, $Z_2 = 1$ — inviting future multifunctional devices' applications [3].

In another striking example, the often-overlooked (blocked by the substrate) flexibility of 2DM leads to unexpected behavior of the ferroelectrics. We introduce a “ferro-flexo” coupling term $\sim P \cdot \kappa$ into the Ginzburg-Landau-Devonshire φ^4 -energy, to connect the ferroelectricity and curvature, κ . The DFT and Monte-Carlo methods allow one to quantify all parameters, so to predict the spontaneous curvature κ_s and the effects on phase transition (rising Curie temperature, domain wall width, etc.) for InP , CuInP_2S_6 and In_2Se_3 as chemically-specific representatives. Polarization switches do bend the layer, converting electrical signal to movement as an actuator, with efficient work-cycle.

References

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Figures

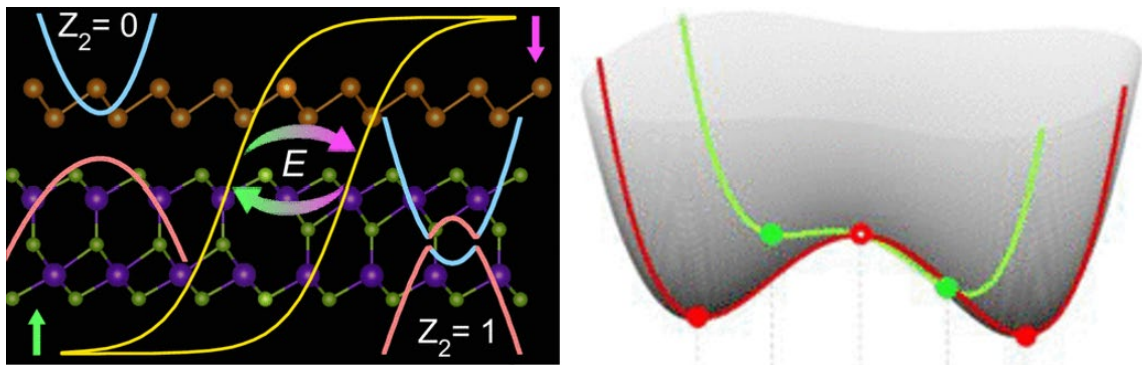


Figure 1: Left: The hysteresis of P , switching the topological state [3]. Right: The generalized φ^4 -potential surface $U(P, \kappa)$ of a 2DM flexo-ferroelectric, flat (green) or with relaxation (red) [4].